



# HETERO JUNCTION FIELD EFFECT TRANSISTOR

# NE3503M04

## C TO Ku BAND SUPER LOW NOISE AND HIGH-GAIN AMPLIFIER N-CHANNEL HJ-FET

### FEATURES

- Super low noise figure and high associated gain  
<R> NF = 0.45 dB TYP.,  $G_a = 12.0$  dB TYP. @  $V_{DS} = 2$  V,  $I_D = 10$  mA,  $f = 12$  GHz
- Flat-lead 4-pin thin-type super minimold (M04) package
- Gate width:  $W_g = 160$   $\mu$ m

### APPLICATIONS

- DBS LNB gain-stage, Mix-stage
- Low noise amplifier for microwave communication system

### ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Marking	Supplying Form
NE3503M04	NE3503M04-A	Flat-lead 4-pin thin-type super minimold (M04) (Pb-Free)	50 pcs (Non reel)	V75	• 8 mm wide embossed taping • Pin 1 (Source), Pin 2 (Drain) face the perforation side of the tape
NE3503M04-T2	NE3503M04-T2-A		3 kpcs/reel		
NE3503M04-T2B	NE3503M04-T2B-A		15 kpcs/reel		

**Remark** To order evaluation samples, contact your nearby sales office.  
Part number for sample order: NE3503M04-A

### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	$V_{DS}$	4.0	V
Gate to Source Voltage	$V_{GS}$	-3.0	V
Drain Current	$I_D$	$I_{DSS}$	mA
Gate Current	$I_G$	80	$\mu$ A
Total Power Dissipation	$P_{tot}$	125	mW
Channel Temperature	$T_{ch}$	+125	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +125	$^\circ\text{C}$

**Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge**

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

**RECOMMENDED OPERATING CONDITIONS (T<sub>A</sub> = +25°C)**

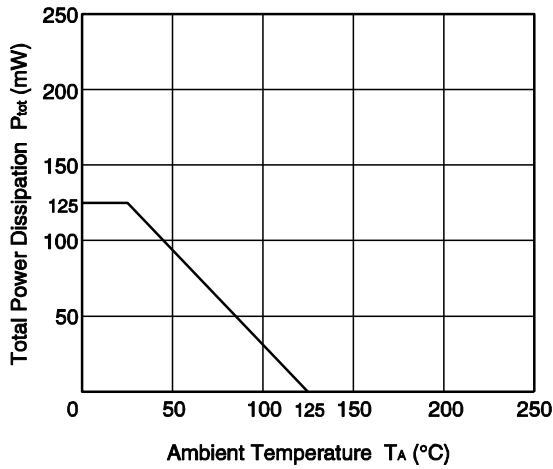
Parameter	Symbol	MIN.	TYP.	MAX.	Unit
<R> Drain to Source Voltage	V <sub>DS</sub>	1	2	3	V
<R> Drain Current	I <sub>D</sub>	5	10	15	mA
Input Power	P <sub>in</sub>	–	–	0	dBm

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C, unless otherwise specified)**

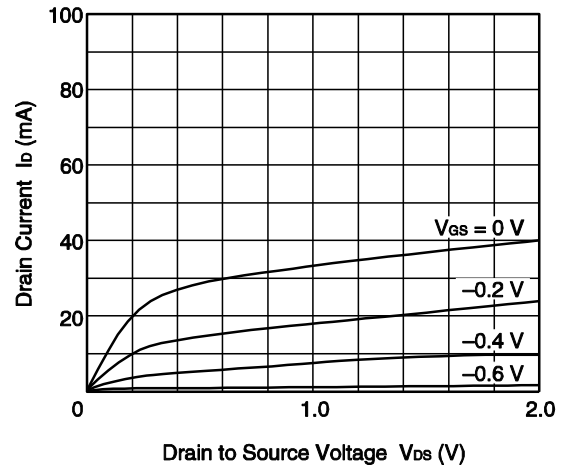
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
<R> Gate to Source Leak Current	I <sub>gso</sub>	V <sub>GS</sub> = -3.0 V	–	0.5	10	μA
<R> Saturated Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 2 V, V <sub>GS</sub> = 0 V	25	40	70	mA
<R> Gate to Source Cutoff Voltage	V <sub>GS (off)</sub>	V <sub>DS</sub> = 2 V, I <sub>D</sub> = 100 μA	-0.2	-0.7	-1.5	V
Transconductance	g <sub>m</sub>	V <sub>DS</sub> = 2 V, I <sub>D</sub> = 10 mA	40	55	–	mS
<R> Noise Figure	NF	V <sub>DS</sub> = 2 V, I <sub>D</sub> = 10 mA, f = 12 GHz	–	0.45	0.65	dB
<R> Associated Gain	G <sub>a</sub>		11.0	12.0	–	dB

TYPICAL CHARACTERISTICS ( $T_A = +25^\circ\text{C}$ , unless otherwise specified)

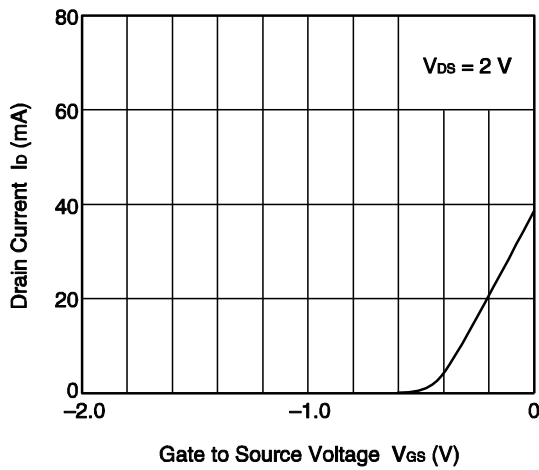
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



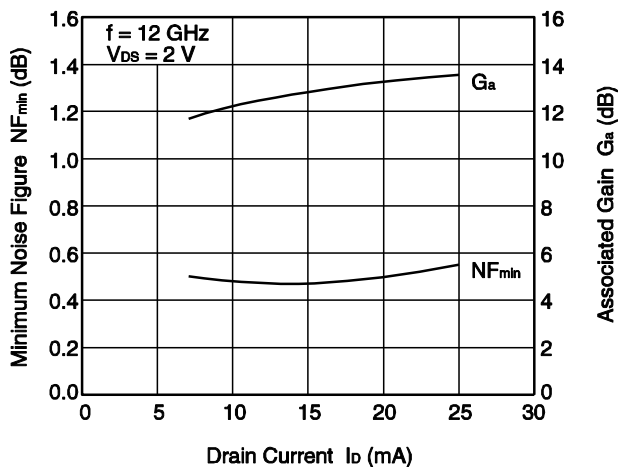
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



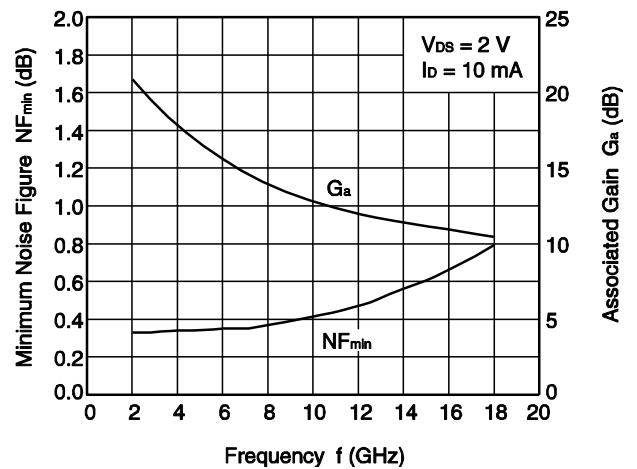
DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT



MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. FREQUENCY



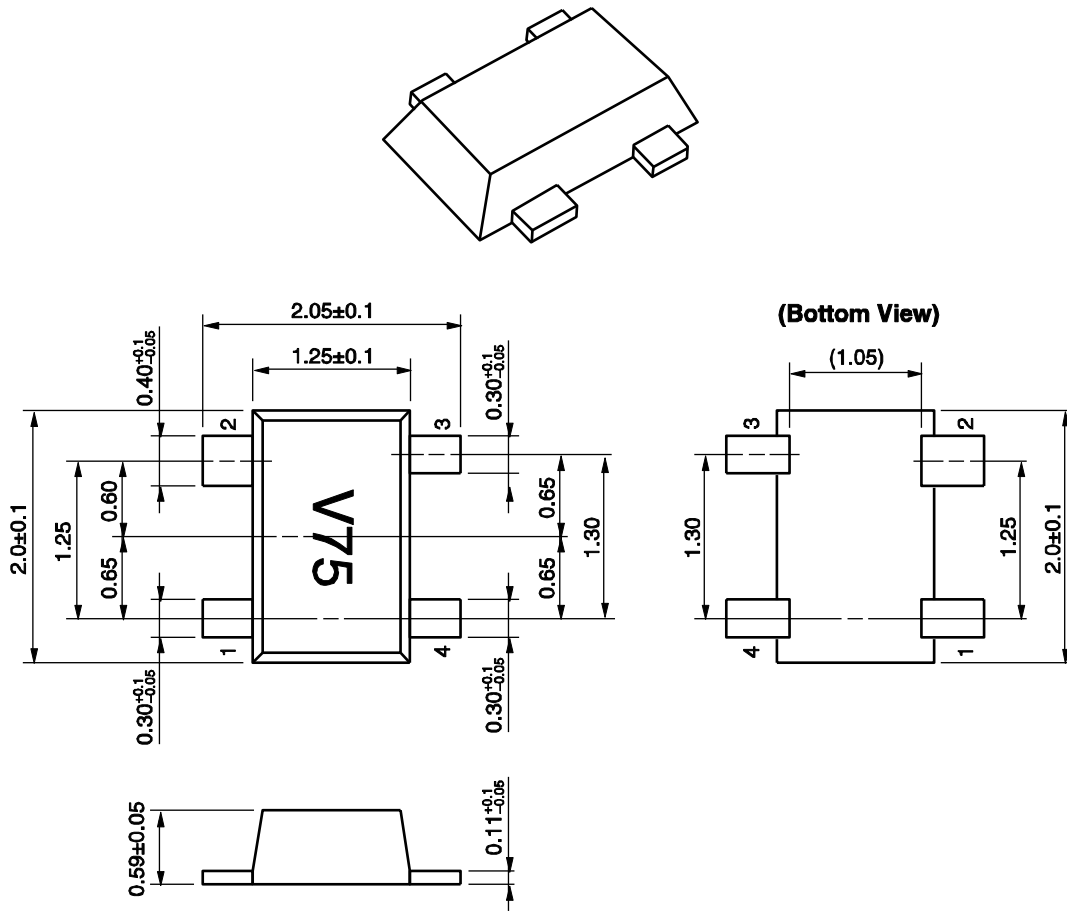
Remark The graphs indicate nominal characteristics.

**S-PARAMETERS**

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- [Click here to download S-parameters.](#)
- [\[RF and Microwave\] ® \[Device Parameters\]](#)
- URL <http://www.necel.com/microwave/en/>

**PACKAGE DIMENSIONS**

**FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)**



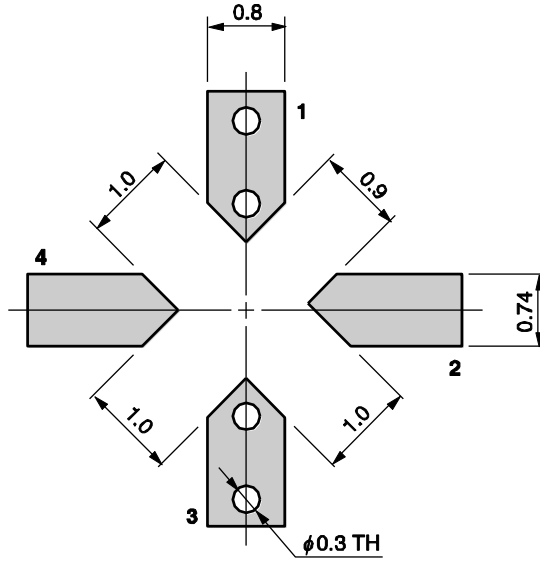
**PIN CONNECTIONS**

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate

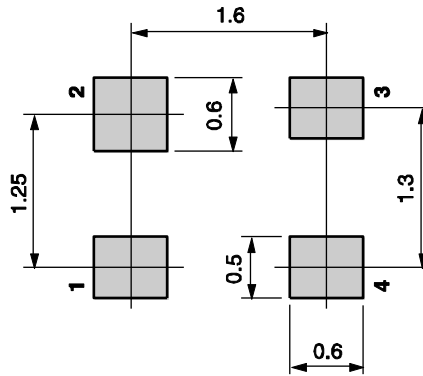
**MOUNTING PAD DIMENSIONS**

**FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)**

–Reference 1–



–Reference 2–



**RECOMMENDED SOLDERING CONDITIONS**

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350

**Caution Do not use different soldering methods together (except for partial heating).**

<p><b>Caution</b> GaAs Products</p>	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> <li>• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.</li> </ul> <ol style="list-style-type: none"> <li>1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.</li> <li>2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.</li> </ol> <ul style="list-style-type: none"> <li>• Do not burn, destroy, cut, crush, or chemically dissolve the product.</li> <li>• Do not lick the product or in any way allow it to enter the mouth.</li> </ul>
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